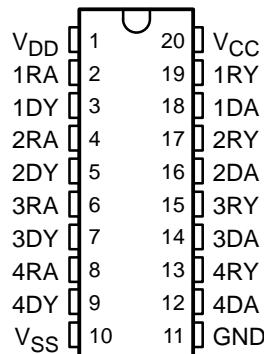


SN65C1154, SN75C1154 QUADRUPLE LOW-POWER DRIVERS/RECEIVERS

SLLS151D – DECEMBER 1988 – REVISED APRIL 2003

- Meet or Exceed the Requirements of TIA/EIA-232-F and ITU Recommendation V.28
- Very Low Power Consumption . . . 5 mW Typ
- Wide Driver Supply Voltage . . . ± 4.5 V to ± 15 V
- Driver Output Slew Rate Limited to 30 V/ μ s Max
- Receiver Input Hysteresis . . . 1000 mV Typ
- Push-Pull Receiver Outputs
- On-Chip Receiver 1- μ s Noise Filter

SN65C1154 . . . N PACKAGE
SN75C1154 . . . DW, N, OR NS PACKAGE
(TOP VIEW)



description/ordering information

The SN65C1154 and SN75C1154 are low-power BiMOS devices containing four independent drivers and receivers that are used to interface data terminal equipment (DTE) with data circuit-terminating equipment (DCE). These devices are designed to conform to TIA/EIA-232-F. The drivers and receivers of the SN65C1154 and SN75C1154 are similar to those of the SN75C188 quadruple driver and SN75C189A quadruple receiver, respectively. The drivers have a controlled output slew rate that is limited to a maximum of 30 V/ μ s and the receivers have filters that reject input noise pulses of shorter than 1 μ s. Both these features eliminate the need for external components.

The SN65C1154 and SN75C1154 have been designed using low-power techniques in a BiMOS technology. In most applications, the receivers contained in these devices interface to single inputs of peripheral devices such as ACEs, UARTs, or microprocessors. By using sampling, such peripheral devices usually are insensitive to the transition times of the input signals. If this is not the case, or for other uses, it is recommended that the SN65C1154 and SN75C1154 receiver outputs be buffered by single Schmitt input gates or single gates of the HCMOS, ALS, or 74F logic families.

ORDERING INFORMATION

T _A	PACKAGE†		ORDERABLE PART NUMBER	TOP-SIDE MARKING
-40°C to 85°C	PDIP (N)	Tube of 20	SN65C1154N	SN65C1154N
0°C to 70°C	PDIP (N)	Tube of 20	SN75C1154N	SN75C1154N
	SOIC (DW)	Tube of 25	SN75C1154DW	SN75C1154
		Reel of 2500	SN75C1154DWR	
	SOP (NS)	Reel of 2000	SN75C1154NSR	SN75C1154

† Package drawings, standard packing quantities, thermal data, symbolization, and PCB design guidelines are available at www.ti.com/sc/package.



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PRODUCTION DATA information is current as of publication date. Products conform to specifications per the terms of Texas Instruments standard warranty. Production processing does not necessarily include testing of all parameters.

 **TEXAS
INSTRUMENTS**

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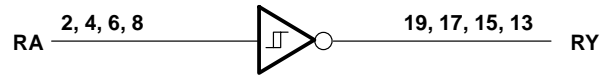
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SN65C1154, SN75C1154 QUADRUPLE LOW-POWER DRIVERS/RECEIVERS

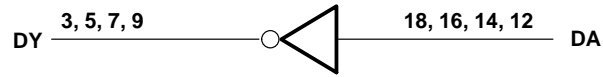
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logic diagram (positive logic)

Typical of Each Receiver



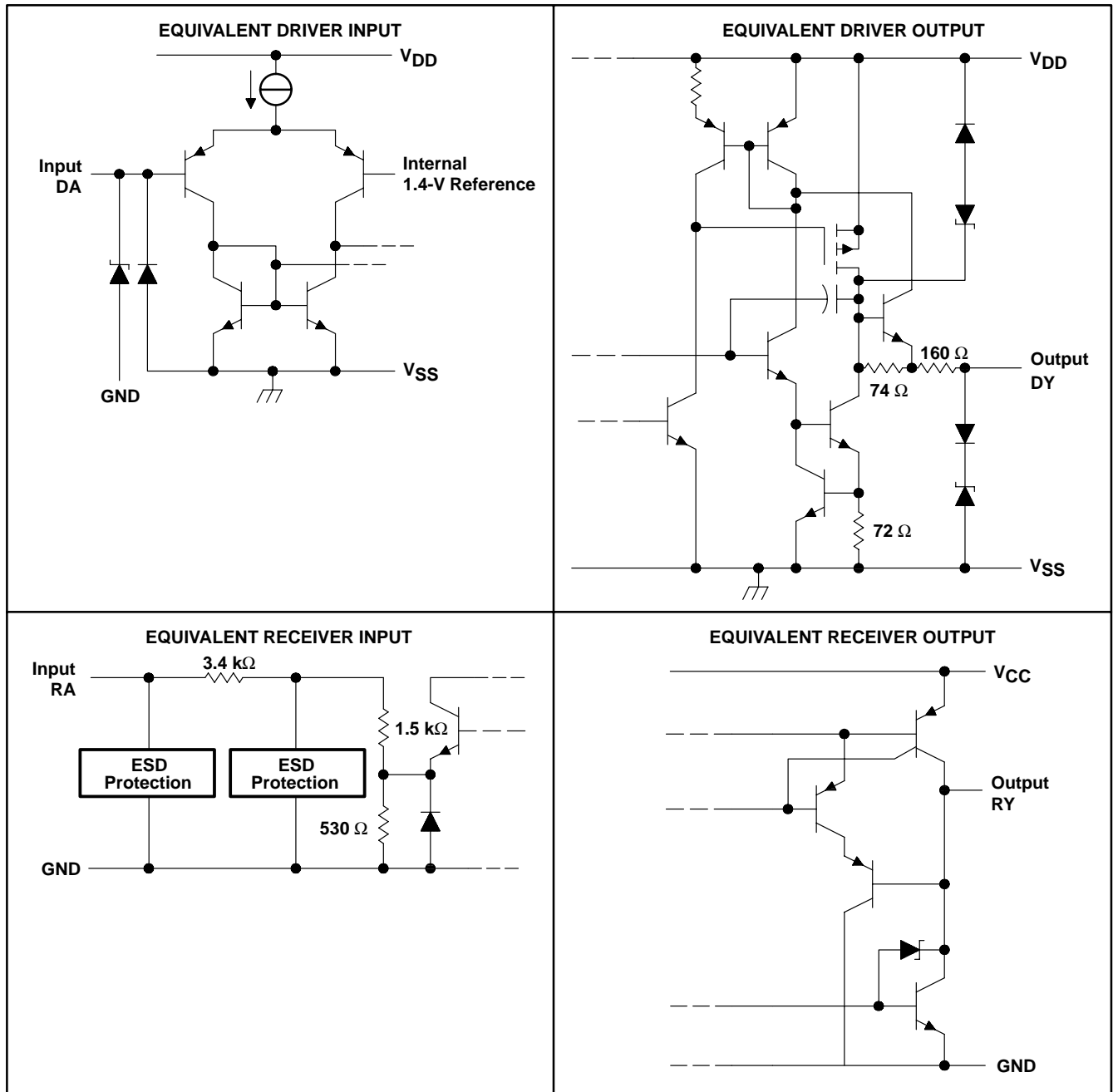
Typical of Each Driver



SN65C1154, SN75C1154 QUADRUPLE LOW-POWER DRIVERS/RECEIVERS

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schematics of inputs and outputs



Resistor values shown are nominal.

SN65C1154, SN75C1154 QUADRUPLE LOW-POWER DRIVERS/RECEIVERS

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absolute maximum ratings over operating free-air temperature range (unless otherwise noted)†

Supply voltage: V_{DD} (see Note 1)	15 V
V_{SS}	-15 V
V_{CC}	7 V
Input voltage range, V_I : Driver	V_{SS} to V_{DD}
Receiver	-30 V to 30 V
Output voltage range, V_O : Driver	($V_{SS} - 6 V$) to ($V_{DD} + 6 V$)
Receiver	-0.3 V to ($V_{CC} + 0.3 V$)
Package thermal impedance, θ_{JA} (see Notes 2 and 3): DW package	58°C/W
N package	69°C/W
NS package	60°C/W
Operating virtual junction temperature, T_J	150°C
Storage temperature range, T_{stg}	-65°C to 150°C
Lead temperature 1,6 mm (1/16 inch) from case for 10 seconds	260°C

† Stresses beyond those listed under “absolute maximum ratings” may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under “recommended operating conditions” is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

- NOTES:
1. All voltage s are with respect to the network GND terminal.
 2. Maximum power dissipation is a function of $T_J(\max)$, θ_{JA} , and T_A . The maximum allowable power dissipation at any allowable ambient temperature is $P_D = (T_J(\max) - T_A)/\theta_{JA}$. Operating at the absolute maximum T_J of 150°C can affect reliability.
 3. The package thermal impedance is calculated in accordance with JESD 51-7.

recommended operating conditions

		MIN	NOM	MAX	UNIT
V_{DD}	Supply voltage	4.5	12	15	V
V_{SS}	Supply voltage	-4.5	-12	-15	V
V_{CC}	Supply voltage	4.5	5	6	V
V_I	Input voltage	Driver	$V_{SS} + 2$	V_{DD}	V
		Receiver		± 25	
V_{IH}	High-level input voltage	2			V
V_{IL}	Low-level input voltage			0.8	V
I_{OH}	High-level output current			-1	mA
I_{OL}	High-level output current			3.2	mA
T_A	Operating free-air temperature	SN65C1154	-40	85	°C
		SN75C1154	0	70	



SN65C1154, SN75C1154 QUADRUPLE LOW-POWER DRIVERS/RECEIVERS

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DRIVER SECTION

electrical characteristics over operating free-air temperature range, $V_{DD} = 12\text{ V}$, $V_{SS} = -12\text{ V}$, $V_{CC} = 5\text{ V} \pm 10\%$ (unless otherwise noted)

PARAMETER	TEST CONDITIONS		MIN	TYP†	MAX	UNIT
V _{OH} High-level output voltage	V _{IL} = 0.8 V, R _L = 3 k Ω , See Figure 1	V _{DD} = 5 V, V _{SS} = -5 V	4	4.5		V
		V _{DD} = 12 V, V _{SS} = -12 V	10	10.8		
V _{OL} Low-level output voltage (see Note 4)	V _{IH} = 2 V, R _L = 3 k Ω , See Figure 1	V _{DD} = 5 V, V _{SS} = -5 V		-4.4	-4	V
		V _{DD} = 12 V, V _{SS} = -12 V		-10.7	-10	
I _{IH} High-level input current	V _I = 5 V, See Figure 2				1	μA
I _{IL} Low-level input current	V _I = 0, See Figure 2				-1	μA
I _{OS(H)} High-level short-circuit output current‡	V _I = 0.8 V, V _O = 0 or V _{SS} , See Figure 1		-7.5	-12	-19.5	mA
I _{OS(L)} Low-level short-circuit output current‡	V _I = 2 V, V _O = 0 or V _{DD} , See Figure 1		7.5	12	19.5	mA
I _{DD} Supply current from V _{DD}	No load, All inputs at 2 V or 0.8 V	V _{DD} = 5 V, V _{SS} = -5 V		115	250	μA
		V _{DD} = 12 V, V _{SS} = -12 V		115	250	
I _{SS} Supply current from V _{SS}	No load, All inputs at 2 V or 0.8 V	V _{DD} = 5 V, V _{SS} = -5 V		-115	-250	μA
		V _{DD} = 12 V, V _{SS} = -12 V		-115	-250	
r _o Output resistance	V _{DD} = V _{SS} = V _{CC} = 0, V _O = -2 V to 2 V, See Note 5		300	400		Ω

† All typical values are at T_A = 25°C.

‡ Not more than one output should be shorted at one time.

NOTES: 4. The algebraic convention, where the more positive (less negative) limit is designated as maximum, is used in this data sheet for logic levels only.

5. Test conditions are those specified by TIA/EIA-232-F.

switching characteristics, $V_{DD} = 12\text{ V}$, $V_{SS} = -12\text{ V}$, $V_{CC} = 5\text{ V} \pm 10\%$, T_A = 25°C (see Figure 3)

PARAMETER	TEST CONDITIONS	MIN	TYP	MAX	UNIT
t _{PLH} Propagation delay time, low- to high-level output§	R _L = 3 to 7 k Ω , C _L = 15 pF		1.2	3	μs
t _{PHL} Propagation delay time, high- to low-level output§	R _L = 3 to 7 k Ω , C _L = 15 pF		2.5	3.5	μs
t _{TLH} Transition time, low- to high-level output¶	R _L = 3 to 7 k Ω , C _L = 15 pF	0.53	2	3.2	μs
t _{THL} Transition time, high- to low-level output¶	R _L = 3 to 7 k Ω , C _L = 15 pF	0.53	2	3.2	μs
t _{TLH} Transition time, low- to high-level output#	R _L = 3 to 7 k Ω , C _L = 2500 pF		1	2	μs
t _{THL} Transition time, high- to low-level output#	R _L = 3 to 7 k Ω , C _L = 2500 pF		1	2	μs
SR Output slew rate	R _L = 3 to 7 k Ω , C _L = 15 pF	4	10	30	V/ μs

§ t_{PHL} and t_{PLH} include the additional time due to on-chip slew rate control and are measured at the 50% points.

¶ Measured between 10% and 90% points of output waveform

Measured between 3 V and -3 V points of output waveform (TIA/EIA-232-F conditions) with all unused inputs tied either high or low



SN65C1154, SN75C1154 QUADRUPLE LOW-POWER DRIVERS/RECEIVERS

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RECEIVER SECTION

electrical characteristics over operating free-air temperature range, $V_{DD} = 12\text{ V}$, $V_{SS} = -12\text{ V}$, $V_{CC} = 5\text{ V} \pm 10\%$ (unless otherwise noted)

PARAMETER		TEST CONDITIONS	MIN	TYP†	MAX	UNIT
V_{IT+}	Positive-going input threshold voltage	See Figure 5	1.7	2.1	2.55	V
V_{IT-}	Negative-going input threshold voltage	See Figure 5	0.65	1	1.25	V
V_{hys}	Input hysteresis voltage ($V_{IT+} - V_{IT-}$)		600	1000		mV
V_{OH}	High-level output voltage	$V_I = 0.75\text{ V}$, $I_{OH} = -20\text{ }\mu\text{A}$, See Figure 5 and Note 6	3.5			V
		$V_I = 0.75\text{ V}$, $I_{OH} = -1\text{ mA}$, See Figure 5	$V_{CC} = 4.5\text{ V}$		2.8 4.4	
			$V_{CC} = 5\text{ V}$		3.8 4.9	
			$V_{CC} = 5.5\text{ V}$		4.3 5.4	
V_{OL}	Low-level output voltage	$V_I = 3\text{ V}$, $I_{OL} = 3.2\text{ mA}$, See Figure 5		0.17	0.4	V
I_{IH}	High-level input current	$V_I = 25\text{ V}$	3.6	4.6	8.3	mA
		$V_I = 3\text{ V}$	0.43	0.55	1	
I_{IL}	Low-level input current	$V_I = -25\text{ V}$	-3.6	-5	-8.3	mA
		$V_I = -3\text{ V}$	-0.43	-0.55	-1	
$I_{OS(H)}$	Short-circuit output at high level	$V_I = 0.75\text{ V}$, $V_O = 0$, See Figure 4		-8	-15	mA
$I_{OS(L)}$	Short-circuit output at low level	$V_I = V_{CC}$, $V_O = V_{CC}$, See Figure 4		13	25	mA
I_{CC}	Supply current from V_{CC}	No load, All inputs at 0 or 5 V	$V_{DD} = 5\text{ V}$, $V_{SS} = -5\text{ V}$	400	600	μA
			$V_{DD} = 12\text{ V}$, $V_{SS} = -12\text{ V}$	400	600	

† All typical values are at $T_A = 25^\circ\text{C}$.

NOTE 6: If the inputs are left unconnected, the receiver interprets this as an input low and the receiver outputs will remain in the high state.

switching characteristics, $V_{DD} = 12\text{ V}$, $V_{SS} = -12\text{ V}$, $V_{CC} = 5\text{ V} \pm 10\%$, $T_A = 25^\circ\text{C}$

PARAMETER		TEST CONDITIONS	MIN	TYP	MAX	UNIT
t_{PLH}	Propagation delay time, low- to high-level output	$C_L = 50\text{ pF}$, $R_L = 5\text{ k}\Omega$, See Figure 6		3	4	μs
t_{PHL}	Propagation delay time, high- to low-level output	$C_L = 50\text{ pF}$, $R_L = 5\text{ k}\Omega$, See Figure 6		3	4	μs
t_{TLH}	Transition time, low- to high-level output	$C_L = 50\text{ pF}$, $R_L = 5\text{ k}\Omega$, See Figure 6		300	450	ns
t_{THL}	Transition time, high- to low-level output	$C_L = 50\text{ pF}$, $R_L = 5\text{ k}\Omega$, See Figure 6		100	300	ns
$t_{w(N)}$	Duration of longest pulse rejected as noise‡	$C_L = 50\text{ pF}$, $R_L = 5\text{ k}\Omega$	1		4	μs

‡ The receiver ignores any positive- or negative-going pulse that is less than the minimum value of $t_{w(N)}$ and accepts any positive- or negative-going pulse greater than the maximum of $t_{w(N)}$.



PARAMETER MEASUREMENT INFORMATION

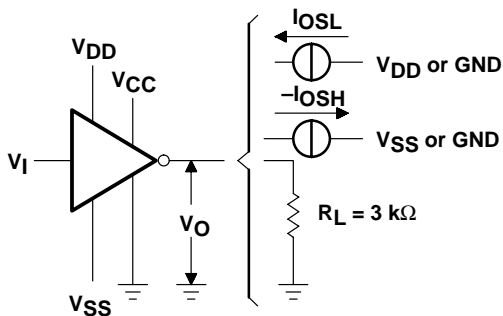


Figure 1. Driver Test Circuit (V_{OH} , V_{OL} , I_{OSL} , I_{OSH})

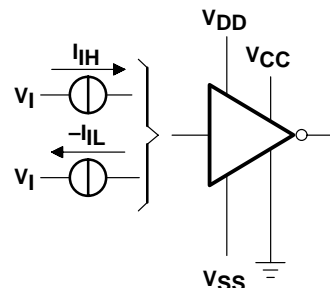
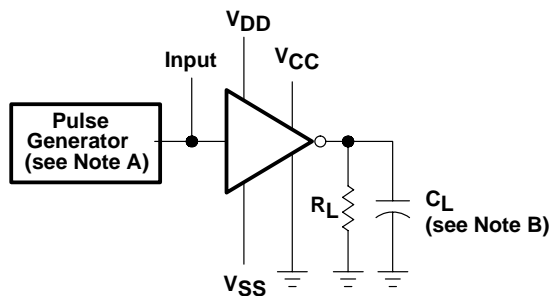
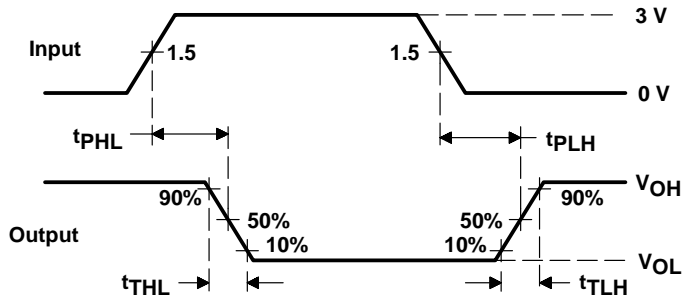


Figure 2. Driver Test Circuit (I_{IL} , I_{IH})



TEST CIRCUIT



VOLTAGE WAVEFORMS

NOTES: A. The pulse generator has the following characteristics: $t_w = 25 \mu s$, PRR = 20 kHz, $Z_O = 50 \Omega$, $t_r = t_f < 50 ns$.
 B. C_L includes probe and jig capacitance.

Figure 3. Driver Test Circuit and Voltage Waveforms

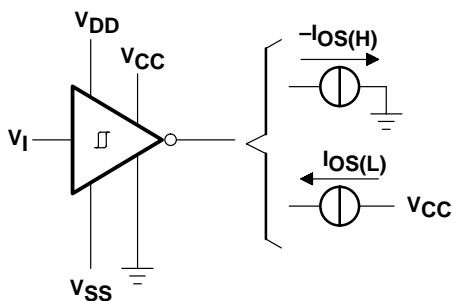


Figure 4. Receiver Test Circuit (I_{OSH} , I_{OSL})

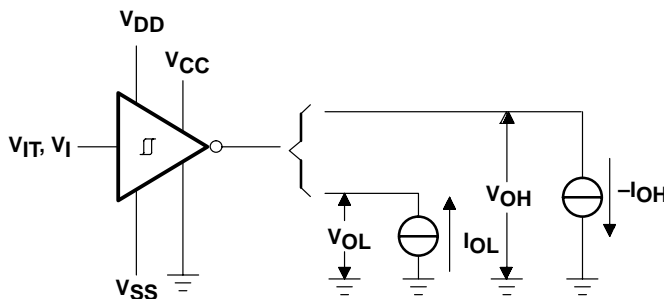
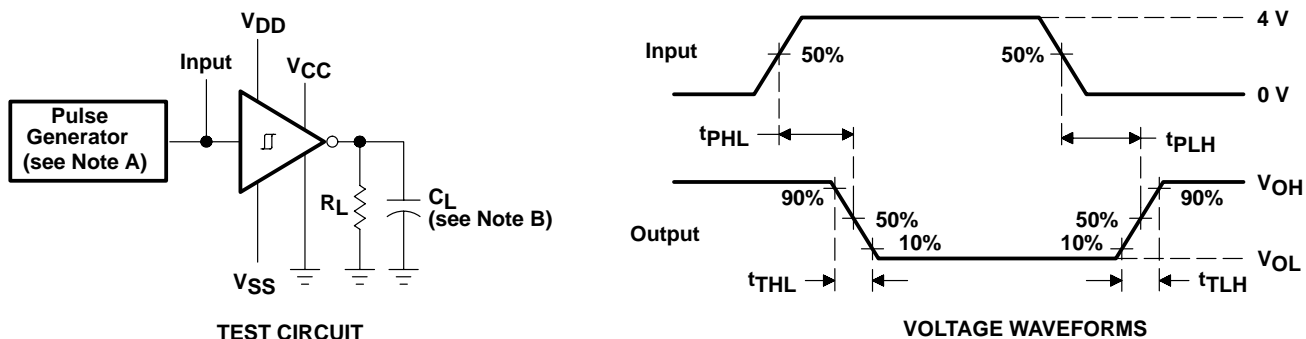


Figure 5. Receiver Test Circuit (V_{IT} , V_{OL} , V_{OH})

SN65C1154, SN75C1154 QUADRUPLE LOW-POWER DRIVERS/RECEIVERS

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PARAMETER MEASUREMENT INFORMATION



NOTES: A. The pulse generator has the following characteristics: $t_w = 25 \mu s$, $PRR = 20 \text{ kHz}$, $Z_O = 50 \Omega$, $t_r = t_f < 50 \text{ ns}$.
 B. C_L includes probe and jig capacitance.

Figure 6. Receiver Test Circuit and Voltage Waveforms

PACKAGING INFORMATION

Orderable Device	Status (1)	Package Type	Package Drawing	Pins	Package Qty	Eco Plan (2)	Lead finish/ Ball material (6)	MSL Peak Temp (3)	Op Temp (°C)	Device Marking (4/5)	Samples
SN65C1154N	ACTIVE	PDIP	N	20	20	RoHS & Green	NIPDAU	N / A for Pkg Type	-40 to 85	SN65C1154N	Samples
SN75C1154DW	ACTIVE	SOIC	DW	20	25	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	0 to 70	SN75C1154	Samples
SN75C1154DWR	ACTIVE	SOIC	DW	20	2000	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	0 to 70	SN75C1154	Samples
SN75C1154N	ACTIVE	PDIP	N	20	20	RoHS & Non-Green	NIPDAU	N / A for Pkg Type	0 to 70	SN75C1154N	Samples

(1) The marketing status values are defined as follows:

ACTIVE: Product device recommended for new designs.

LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.

PREVIEW: Device has been announced but is not in production. Samples may or may not be available.

OBSELETE: TI has discontinued the production of the device.

(2) **RoHS:** TI defines "RoHS" to mean semiconductor products that are compliant with the current EU RoHS requirements for all 10 RoHS substances, including the requirement that RoHS substance do not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, "RoHS" products are suitable for use in specified lead-free processes. TI may reference these types of products as "Pb-Free".

RoHS Exempt: TI defines "RoHS Exempt" to mean products that contain lead but are compliant with EU RoHS pursuant to a specific EU RoHS exemption.

Green: TI defines "Green" to mean the content of Chlorine (Cl) and Bromine (Br) based flame retardants meet JS709B low halogen requirements of <=1000ppm threshold. Antimony trioxide based flame retardants must also meet the <=1000ppm threshold requirement.

(3) MSL, Peak Temp. - The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.

(4) There may be additional marking, which relates to the logo, the lot trace code information, or the environmental category on the device.

(5) Multiple Device Markings will be inside parentheses. Only one Device Marking contained in parentheses and separated by a "~" will appear on a device. If a line is indented then it is a continuation of the previous line and the two combined represent the entire Device Marking for that device.

(6) Lead finish/Ball material - Orderable Devices may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead finish/Ball material values may wrap to two lines if the finish value exceeds the maximum column width.

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TAPE AND REEL INFORMATION

QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE

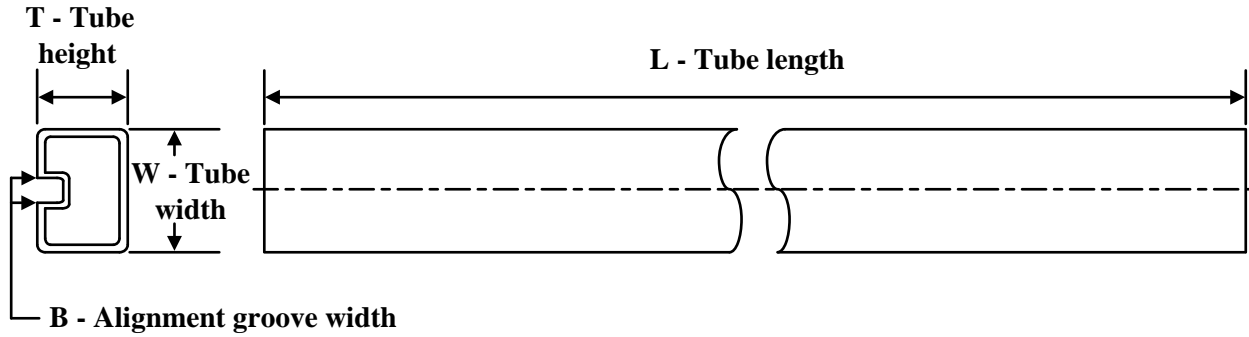

*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
SN75C1154DWR	SOIC	DW	20	2000	330.0	24.4	10.8	13.3	2.7	12.0	24.0	Q1

TAPE AND REEL BOX DIMENSIONS


*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
SN75C1154DWR	SOIC	DW	20	2000	350.0	350.0	43.0

TUBE


*All dimensions are nominal

Device	Package Name	Package Type	Pins	SPQ	L (mm)	W (mm)	T (μm)	B (mm)
SN65C1154N	N	PDIP	20	20	506	13.97	11230	4.32
SN75C1154DW	DW	SOIC	20	25	506.98	12.7	4826	6.6
SN75C1154N	N	PDIP	20	20	506	13.97	11230	4.32

N (R-PDIP-T**)

PLASTIC DUAL-IN-LINE PACKAGE

16 PINS SHOWN



- NOTES:
- A. All linear dimensions are in inches (millimeters).
 - B. This drawing is subject to change without notice.
 - Falls within JEDEC MS-001, except 18 and 20 pin minimum body length (Dim A).
 - The 20 pin end lead shoulder width is a vendor option, either half or full width.

DW0020A



PACKAGE OUTLINE

SOIC - 2.65 mm max height

SOIC



4220724/A 05/2016

NOTES:

1. All linear dimensions are in millimeters. Dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.
2. This drawing is subject to change without notice.
3. This dimension does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed 0.15 mm per side.
4. This dimension does not include interlead flash. Interlead flash shall not exceed 0.43 mm per side.
5. Reference JEDEC registration MS-013.

EXAMPLE BOARD LAYOUT

DW0020A

SOIC - 2.65 mm max height

SOIC



LAND PATTERN EXAMPLE
SCALE:6X



SOLDER MASK DETAILS

4220724/A 05/2016

NOTES: (continued)

- 6. Publication IPC-7351 may have alternate designs.
- 7. Solder mask tolerances between and around signal pads can vary based on board fabrication site.

EXAMPLE STENCIL DESIGN

DW0020A

SOIC - 2.65 mm max height

SOIC



SOLDER PASTE EXAMPLE
BASED ON 0.125 mm THICK STENCIL
SCALE:6X

4220724/A 05/2016

NOTES: (continued)

8. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.
9. Board assembly site may have different recommendations for stencil design.

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